



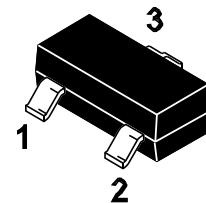
PJM10H01PSA

P-Channel Enhancement Mode Power MOSFET

Features

- Fast switching
- Low gate charge and $R_{DS(on)}$
- $V_{DS} = -100V, I_D = -1A$
- $R_{DS(on)} < 650m\Omega @ V_{GS} = -10V$

SOT-23



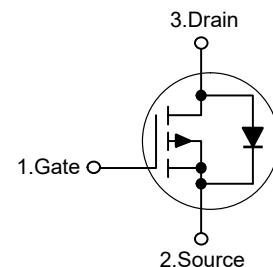
1. Gate 2. Source 3. Drain

Marking Code: 0101

Applications

- PWM applications
- Load switch
- Power management

Schematic Diagram



Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

| Parameter | Symbol | Value | Unit |
|---------------------------------------|-----------|-------------|------|
| Drain-Source Voltage | $-V_{DS}$ | 100 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | $-I_D$ | 1 | A |
| Drain Current-Pulsed ^{Note1} | $-I_{DM}$ | 1.5 | A |
| Maximum Power Dissipation | P_D | 0.5 | W |
| Junction Temperature | T_J | 150 | °C |
| Storage Temperature Range | T_{STG} | -55 to +150 | °C |

Thermal Characteristics

| | | | |
|--|-----------------|-----|------|
| Thermal Resistance, Junction-to-Ambient ^{Note2} | $R_{\theta JA}$ | 250 | °C/W |
|--|-----------------|-----|------|



PJM10H01PSA

P-Channel Enhancement Mode Power MOSFET

Electrical Characteristics

(Ta=25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|---|-----------------------|---|------|------|------|------|
| Static Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | -V _{(BR)DSS} | V _{GS} =0V, I _D =-250μA | 100 | -- | -- | V |
| Zero Gate Voltage Drain Current | -I _{DSS} | V _{DS} =-80V, V _{GS} =0V | -- | -- | 100 | nA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | -- | -- | ±100 | nA |
| Gate Threshold Voltage ^{Note3} | -V _{GS(th)} | V _{DS} =V _{GS} , I _D =-250μA | 1 | -- | 2.5 | V |
| Drain-Source On-Resistance ^{Note3} | R _{DS(on)} | V _{GS} =-10V, I _D =-1A | -- | -- | 650 | mΩ |
| | | V _{GS} =-6V, I _D =-0.5A | -- | -- | 700 | mΩ |
| Switching Characteristics | | | | | | |
| Turn-on Delay Time | t _{d(on)} | V _{DD} =-50V, I _D =-1A V _{GEN} =-10V, R _L =33Ω, R _G =6Ω | -- | 7 | 11 | nS |
| Turn-on Rise Time | t _r | | -- | 11 | 17 | nS |
| Turn-off Delay Time | t _{d(off)} | | -- | 9 | 15 | nS |
| Turn-off Fall Time | t _f | | -- | 10 | 15 | nS |
| Total Gate Charge | Q _g | V _{DD} =-50V, I _D =-1A, V _{GS} =-10V | -- | 3.3 | 4 | nC |
| Gate-Source Charge | Q _{gs} | | -- | 0.47 | -- | nC |
| Gate-Drain Charge | Q _{gd} | | -- | 1.45 | -- | nC |
| Source-Drain Diode Characteristics | | | | | | |
| Diode Forward Voltage ^{Note3} | -V _{SD} | V _{GS} =0V, I _S =-0.5A | -- | -- | 1.3 | V |
| Diode Forward Current ^{Note2} | -I _S | | -- | -- | 1 | A |

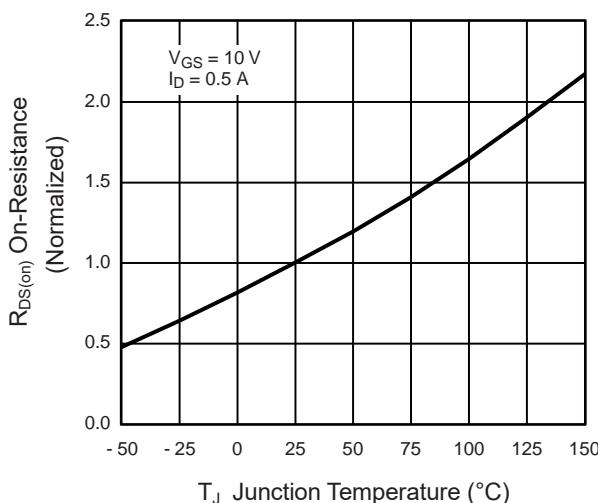
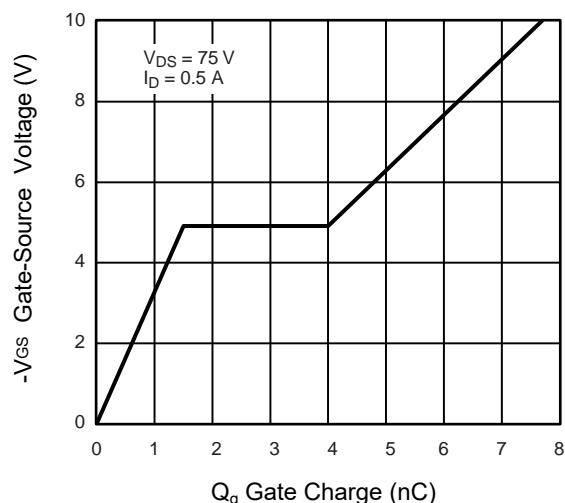
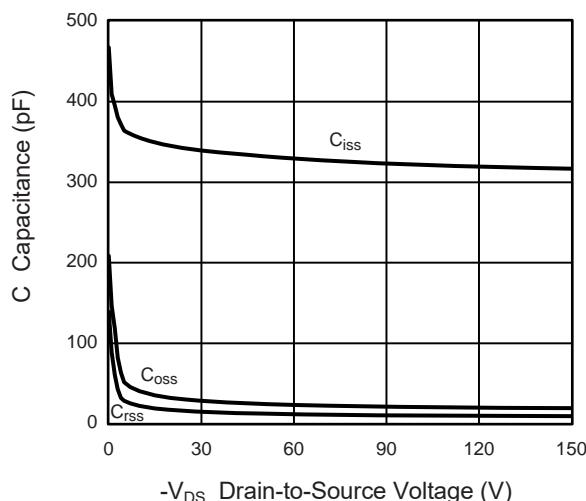
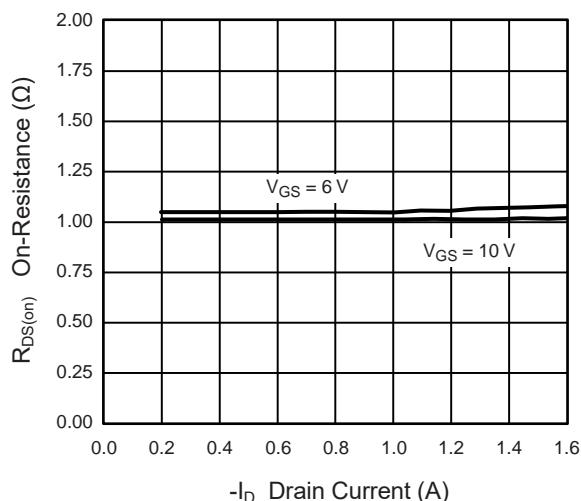
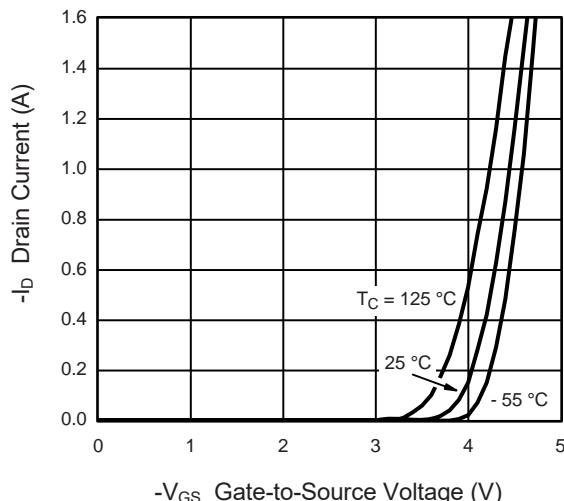
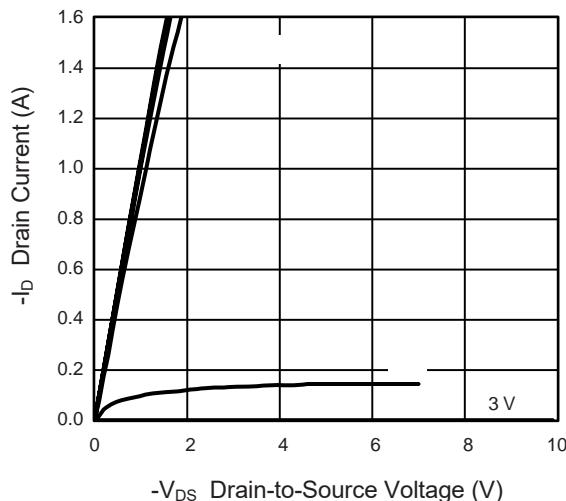
Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.



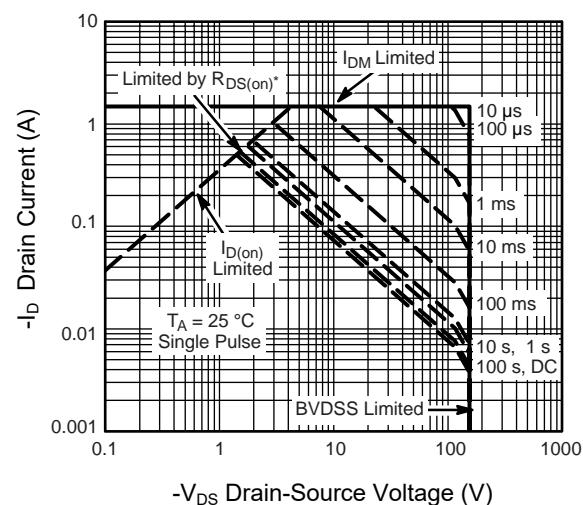
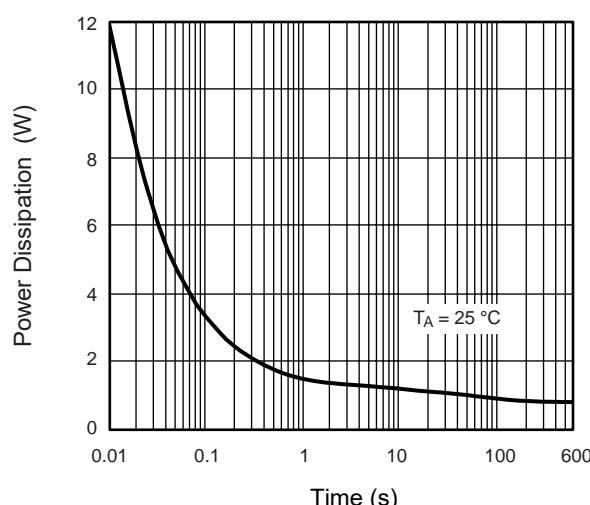
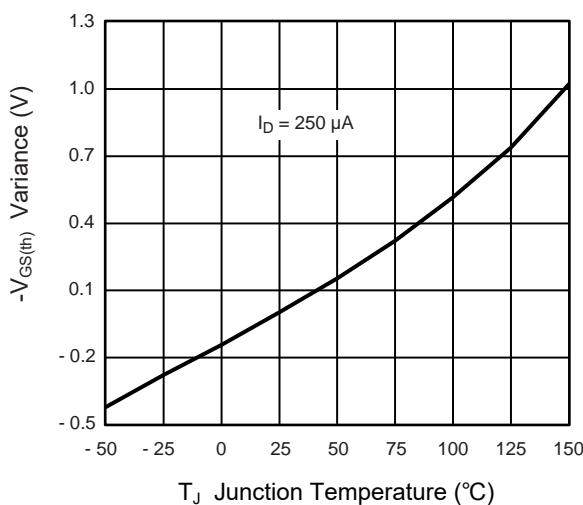
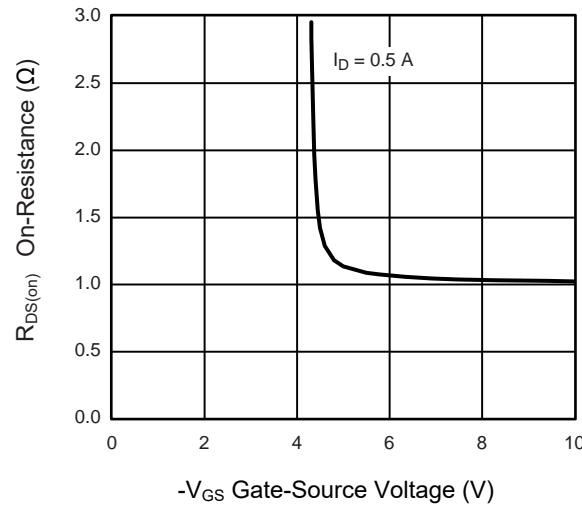
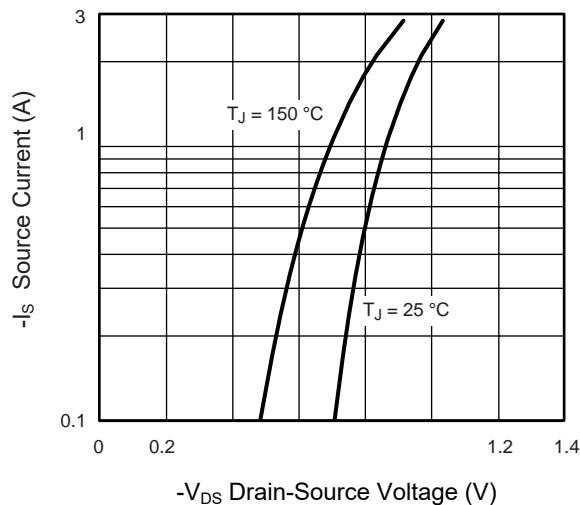
Typical Characteristic Curves





PJM10H01PSA

P-Channel Enhancement Mode Power MOSFET





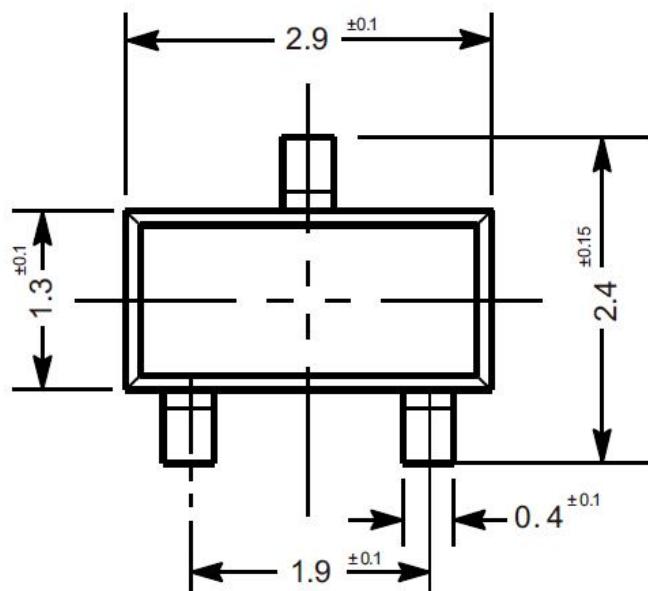
PJM10H01PSA

P-Channel Enhancement Mode Power MOSFET

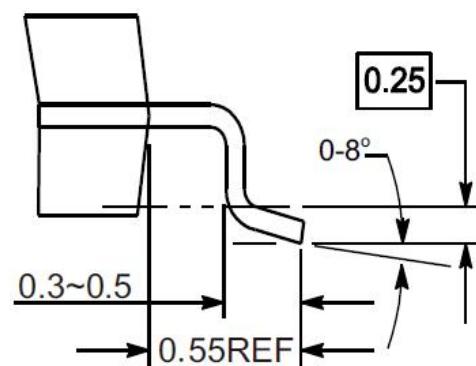
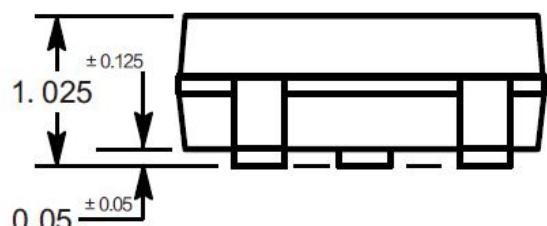
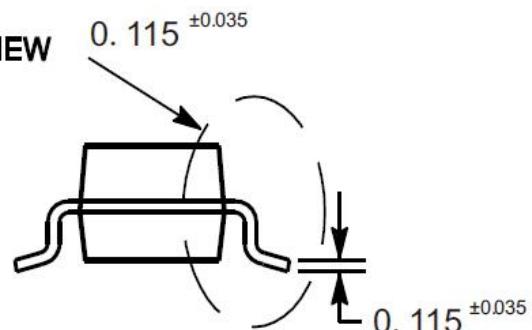
Package Outline

SOT-23

Dimensions in mm



SEE VIEW



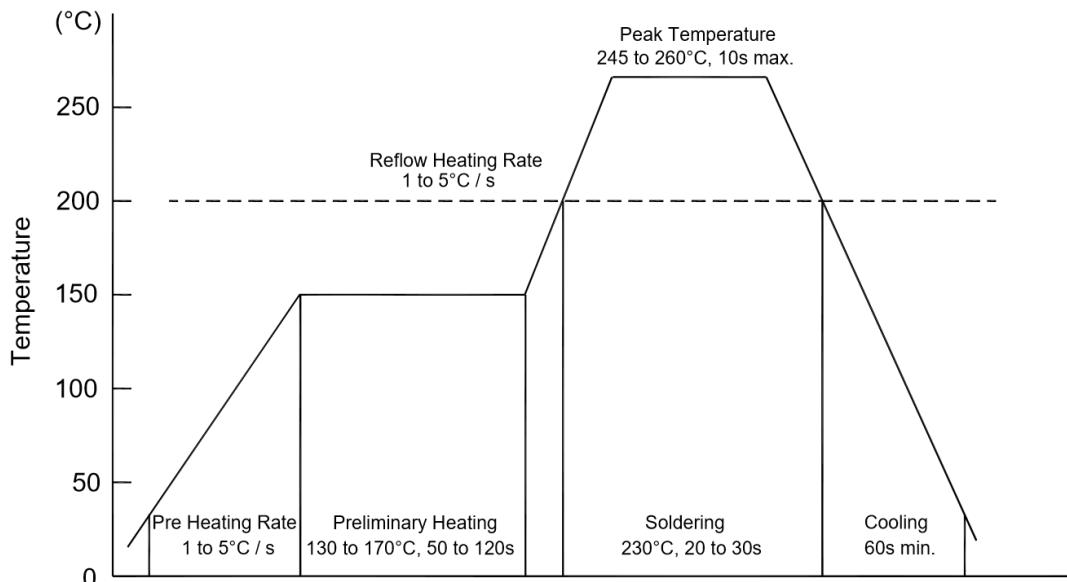
VIEW C

Ordering Information

| Device | Package | Shipping |
|-------------|---------|-----------------------|
| PJM10H01PSA | SOT-23 | 3,000PCS/Reel&7inches |

Conditions of Soldering and Storage

◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

◆ Conditions of hand soldering

- Temperature: 370 °C
- Time: 3s max.
- Times: one time

◆ Storage conditions

- **Temperature**
5 to 40 °C
- **Humidity**
30 to 80% RH
- **Recommended period**
One year after manufacturing

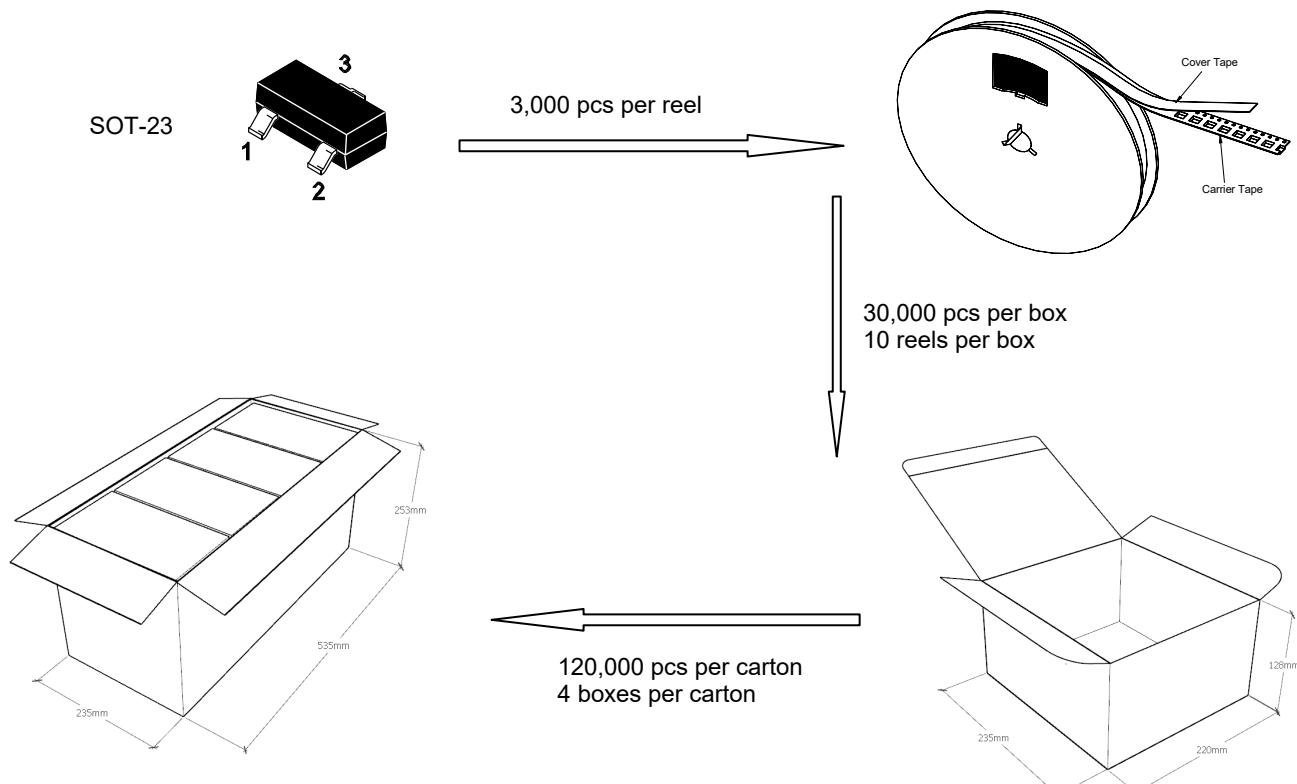


PJM10H01PSA

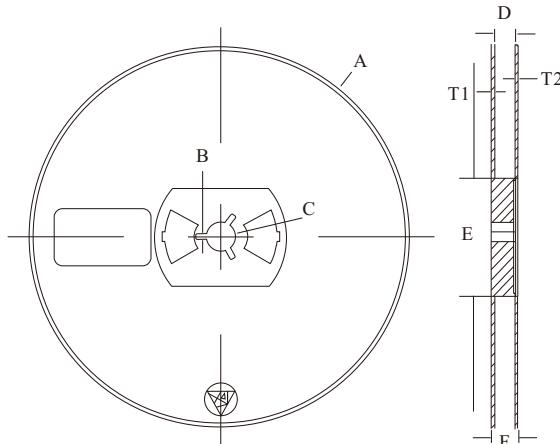
P-Channel Enhancement Mode Power MOSFET

Package Specifications

- The method of packaging

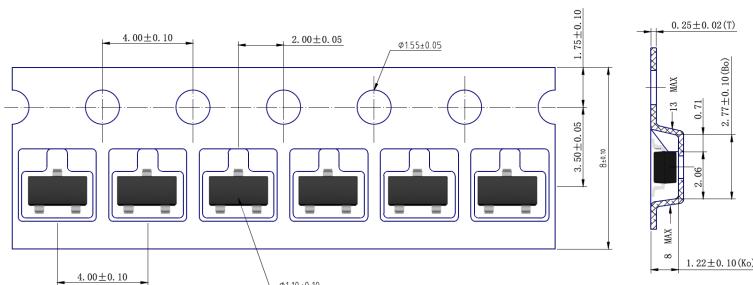


◆ Embossed tape and reel data



| Symbol | Value (unit: mm) |
|--------|----------------------------|
| A | $\varnothing 177.8 \pm 1$ |
| B | 2.7 ± 0.2 |
| C | $\varnothing 13.5 \pm 0.2$ |
| E | $\varnothing 54.5 \pm 0.2$ |
| F | 12.3 ± 0.3 |
| D | $9.6 +2/-0.3$ |
| T1 | 1.0 ± 0.2 |
| T2 | 1.2 ± 0.2 |

Reel (7")



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Pingjingsemi manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [NTNS3A92PZT5G](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#) [AOD464](#)
[2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#)
[IPS70R2K0CEAKMA1](#) [BSF024N03LT3 G](#) [PSMN4R2-30MLD](#) [TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#)
[EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMC2700UDMQ-7](#)
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#)
[DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [IRF40H233XTMA1](#) [IPSA70R950CEAKMA1](#) [IPSA70R2K0CEAKMA1](#) [STU5N65M6](#)
[C3M0021120D](#) [DMN6022SSD-13](#)